

## **isc Silicon NPN Power Transistor**

# KSD1408

### DESCRIPTION

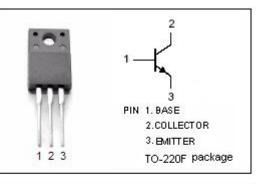
- Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= 1.5V(Max)@ I<sub>C</sub>= 3A
- Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 80V (Min)
- Complement to Type KSB1017
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

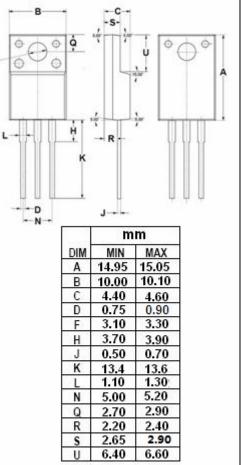
### **APPLICATIONS**

· Designed for power amplifier applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

	SYMBOL	PARAMETER	VALUE	UNIT	F
	V <sub>CBO</sub>	Collector-Base Voltage	80	V	3
	V <sub>CEO</sub>	Collector-Emitter Voltage	80	V	
	V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
	Ic	Collector Current-Continuous	4	A	
_	Ι <sub>Β</sub>	Base Current-Continuous	0.4	A	
_	Pc	Collector Power Dissipation @ Tc=25°C	25	W	
_	TJ	Junction Temperature	150	°C	
_	T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			30	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
hfe-1	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	40		240	
hfe-2	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	15			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		90		pF
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		8		MHz

#### h<sub>FE</sub> classifications

R	0	Y		
40-80	70-140	120-240		

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